

FMW3 / FMW4 / IMX8

Transistors

General purpose (dual transistors)

FMW3 / FMW4 / IMX8

●Features

- 1) Two 2SC3906K chips in an SMT package.
- 2) High breakdown voltage.

●Absolute maximum ratings (Ta = 25°C)

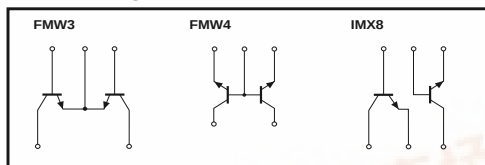
Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CB0}	120	V
Collector-emitter voltage	V _{CE0}	120	V
Emitter-base voltage	V _{EB0}	5	V
Collector current	I _C	50	mA
Power dissipation	P _C	300(TOTAL)	mW *
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55~+150	°C

* 200mW per element must not be exceeded.

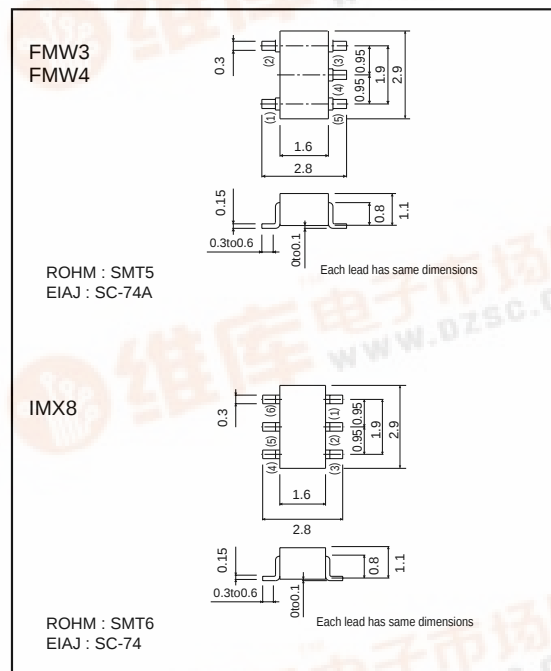
●Package, marking, and packaging specifications

Part No.	FMW3	FMW4	IMX8
Package	SMT5	SMT5	SMT6
Marking	W3	W4	X4
Code	T148	T148	T108
Basic ordering unit (pieces)	3000	3000	3000

●Circuit diagrams



●External dimensions (Units : mm)



●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	120	—	—	V	I _C =50μA
Collector-emitter breakdown voltage	BV _{CE0}	120	—	—	V	I _C =1mA
Emitter-base breakdown voltage	BV _{EB0}	5	—	—	V	I _E =50μA
Collector cutoff current	I _{CB0}	—	—	0.5	μA	V _{CB} =100V
Emitter cutoff current	I _{EB0}	—	—	0.5	μA	V _{EB} =4V
DC current transfer ratio	h _{FE}	180	—	820	—	V _{CE} =6V, I _C =2mA
Transition frequency	f _T	—	140	—	MHz	V _{CE} =12V, I _E =2mA, f=100MHz *
Collector-emitter saturation voltage	V _{CE(sat)}	—	—	0.5	V	I _C /I _E =10mA/1mA

* Transition frequency of the device